

PRODUCT CHARACTERISTICS

V_{DSS}	60V
$R_{DS(ON)}$ Typ(@ $V_{GS}=10V$)	26m Ω
$R_{DS(ON)}$ Typ(@ $V_{GS}=4.5V$)	33m Ω
I_D	30A

APPLICATIONS

- * Motor Control
- * High Performance SMPS
- * DC/DC Converter

FEATURE

- * Low Gate Charge
- * Ultra-low $R_{DS(ON)}$

ORDER INFORMATION

Order Codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT30N06D	TO-252	2500 pieces/Reel

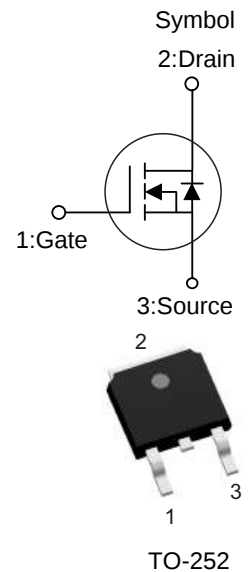
ABSOLUTE MAXIMUM RATINGS($T_A=25^{\circ}C$, unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current Continuous(@ $V_{GS}=10V$, $T_A=25^{\circ}C$)	I_D	30	A
Drain Current Pulsed	I_{DM}	120	A
Avalanche Energy *	E_{AS}	60	mJ
Power Dissipation	P_D	50	W
Junction Temperature	T_J	+150	$^{\circ}C$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}C$

THERMAL CHARACTERISTICS

Parameter	Symbol	Typ	Unit
Junction to Case	R_{thJC}	2.5	$^{\circ}C/W$

Note: * EAS condition: $T_J=25^{\circ}C$, $V_{DD}=30V$, $V_G=10V$, $L=0.5mH$, $R_g=25\Omega$



■ ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Off characteristics						
Drain to Source Breakdown Voltage	V _{DSS}	V _{GS} =0V, I _D =250μA	60	-	-	V
Drain to Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate to Source Forward Leakage	I _{GSS(F)}	V _{DS} =0V, V _{GS} =+20V	-	-	100	nA
Gate to Source Reverse Leakage	I _{GSS(R)}	V _{DS} =0V, V _{GS} =-20V	-	-	-100	nA
On characteristics						
Drain to Source On-Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	26	29	mΩ
		V _{GS} =4.5V, I _D =20A	-	33	40	mΩ
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	1	1.6	2.5	V
Dynamic characteristics						
Gate capacitance	R _g	V _{GS} =0V, V _{DS} =0V ,f=1.0MHz	-	1.4	-	Ω
Forward Transconductance	g _{fs}	V _{DS} =10V, I _D =2 A	-	5	-	S
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V f=1.0MHz	-	938	-	pF
Output Capacitance	C _{oss}		-	80	-	pF
Reverse Transfer Capacitance	C _{rss}		-	40	-	pF
Resistive Switching Characteristics						
Turn-on Delay Time	t _{d(ON)}	I _D =30A, V _{DS} =30V R _G =1.6Ω ,V _{GS} =10V	-	4.8	-	ns
Rise Time	t _r		-	16.6	-	ns
Turn-off Delay Time	t _{d(OFF)}		-	28	-	ns
Fall Time	t _f		-	19	-	ns
Total Gate Charge	Q _g	I _D =30A, V _{DS} =30V V _{GS} =10V	-	40	-	nC
Gate to Source Charge	Q _{gs}		-	8.4	-	nC
Gate to Drain("Miller") Charge	Q _{gd}		-	15	-	nC
Source-Drain Diode Characteristics						
Continuous Source Current(Body Diode)	I _s		-	-	30	A
Maximum Pulsed Current(Body Diode)	I _{SM}		-	-	120	A
Diode Forward Voltage	V _{SD}	I _{SD} =1A, V _{GS} =0V	-	0.74	1.2	V
Reverse Recovery Time	t _{rr}	I _{SD} =30 A, T _J =25°C dI/dt=100A/μs	-	32	-	ns
Reverse Recovery Charge	Q _{rr}		-	58	-	nC

■ TYPICAL CHARACTERISTICS

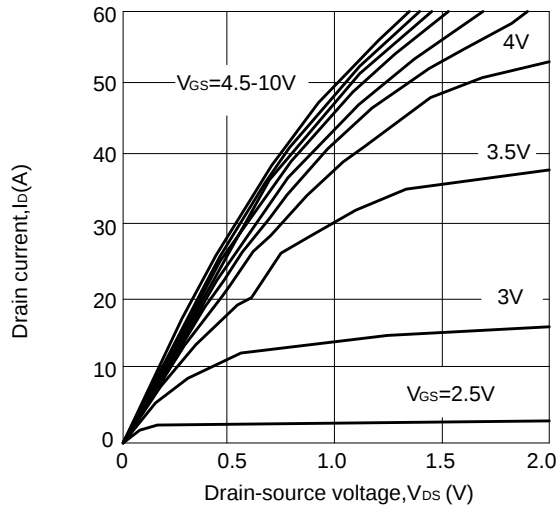


Figure 1: Drain current vs. drain-source voltage

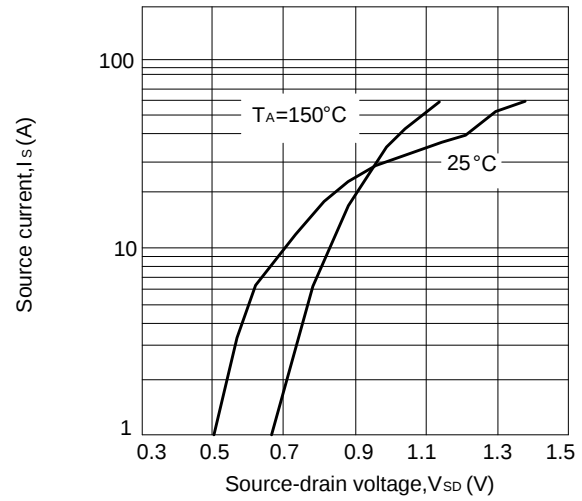


Figure 2: Source current vs. source-drain voltage

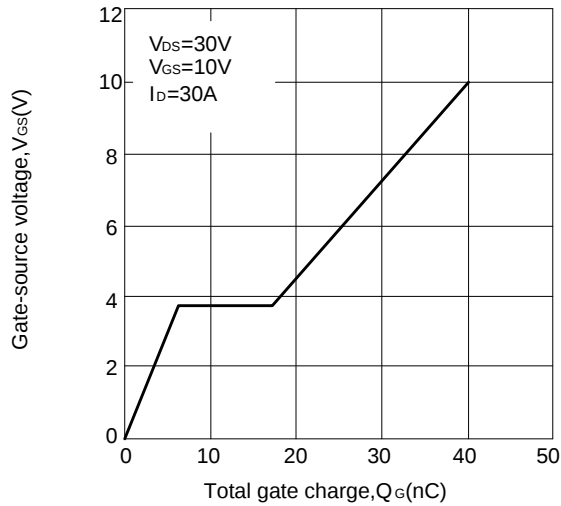


Figure 3: Gate charge characteristics

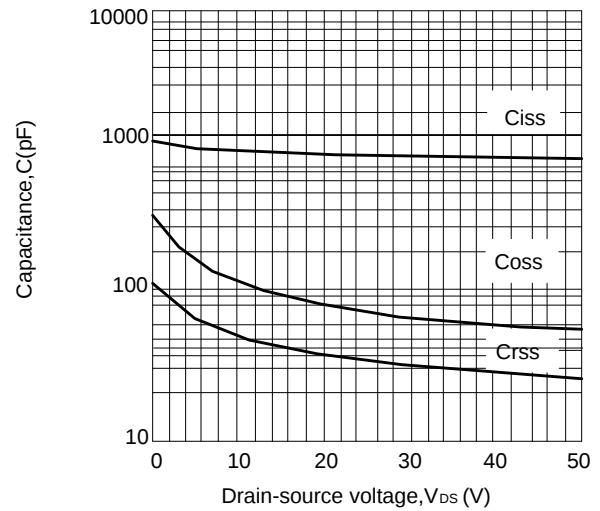


Figure 4: Capacitance characteristics

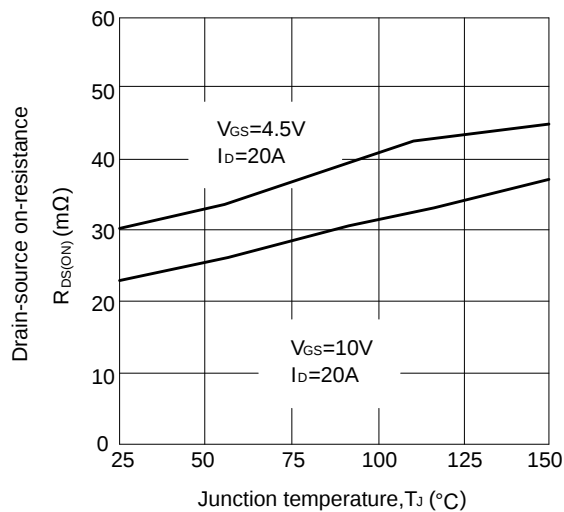


Figure 5: Drain-source on-resistance vs. junction temperature

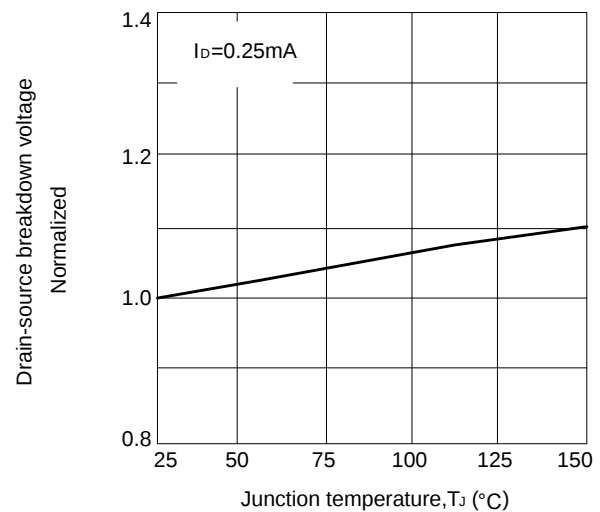


Figure 6: Break voltage vs. junction temperature

■ TYPICAL CHARACTERISTICS(Cont.)

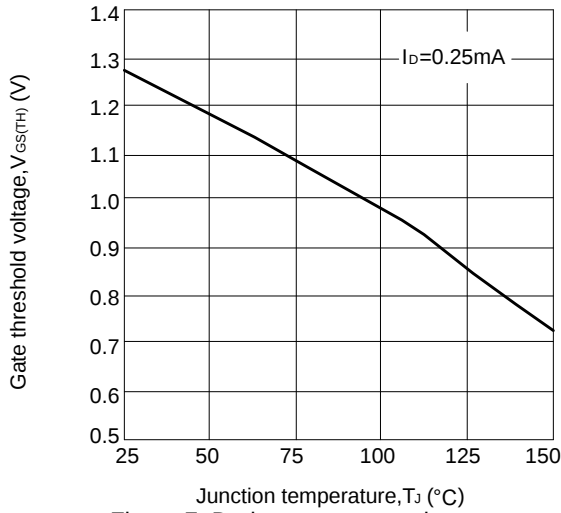


Figure 7: Drain-source on-resistance vs. junction temperature

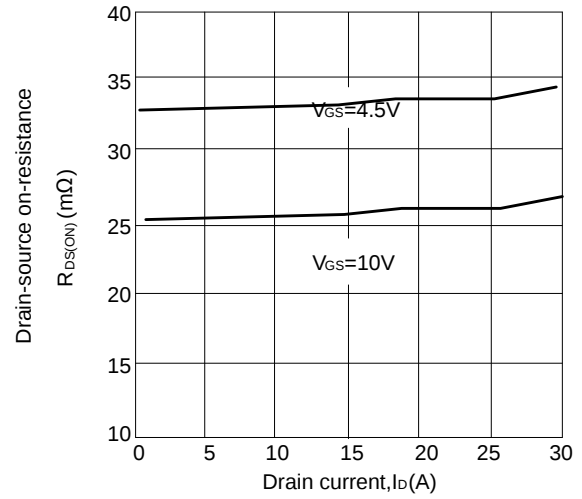


Figure 8: Drain-source on-resistance vs. drain current

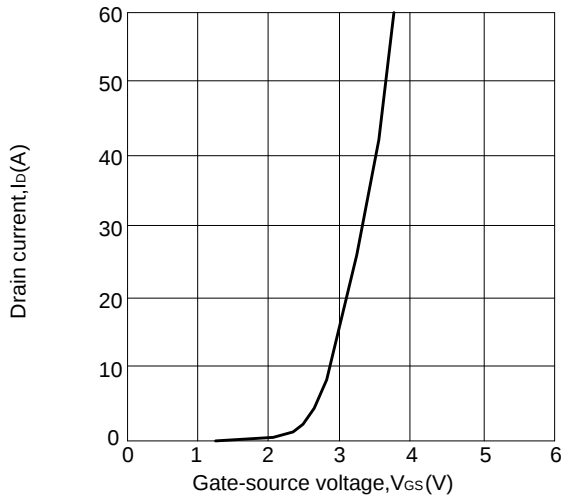


Figure 9: Drain current vs. gate-source voltage

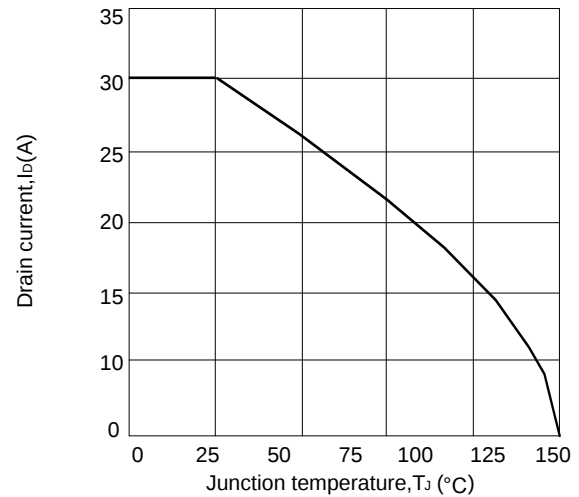


Figure 10: Drain current vs. junction temperature

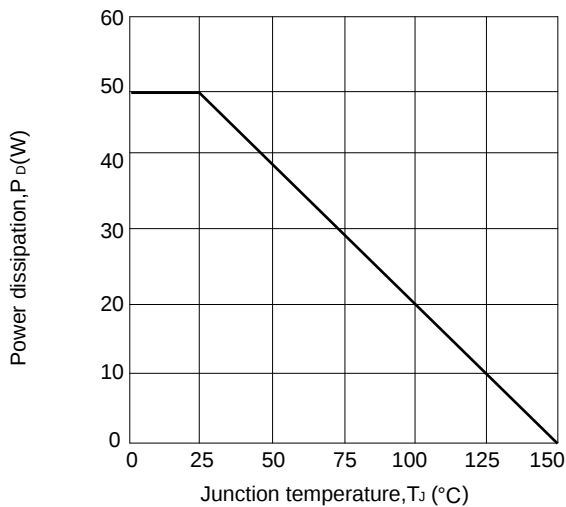


Figure 11: Power dissipation vs. junction temperature

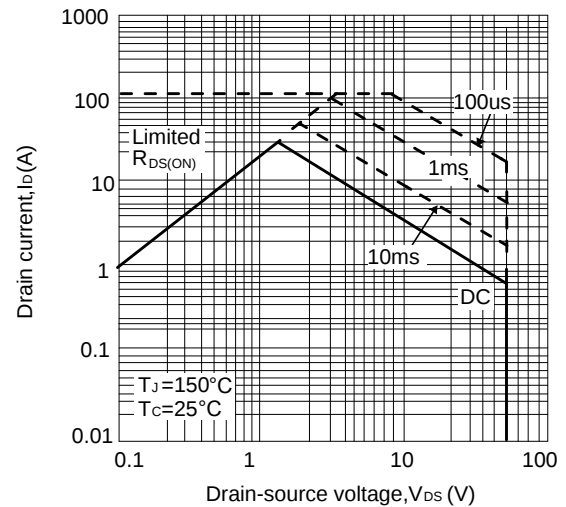


Figure 12: Safe operating safe

■ TO-252 PACKAGE OUTLINE DIMENSIONS

